TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2406

Power Amplifier Applications

- High power dissipation: $PC = 25 \text{ W} \text{ (Tc} = 25^{\circ}\text{C)}$
- Good hFE linearity

Absolute Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	80) \
Collector-emitter voltage	V _{CEO}	80	$(\nearrow \land$
Emitter-base voltage	V _{EBO}	5	$\langle \psi \rangle$
Collector current	IC	4	Ą
Base current	ΙΒ	0.4	A
Collector power dissipation	Pc	25	W
(Tc = 25°C)	FC	25	VV
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 to 150	Í,

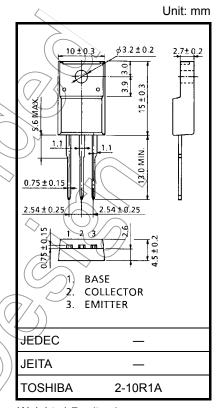
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

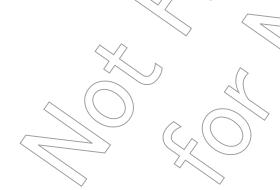
Weight: 1.7 g (typ.)

operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook

("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



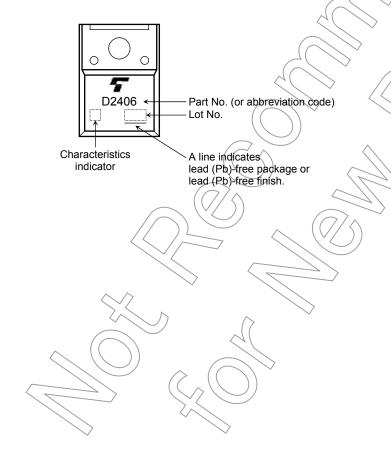


Electrical Characteristics (Tc = 25°C)

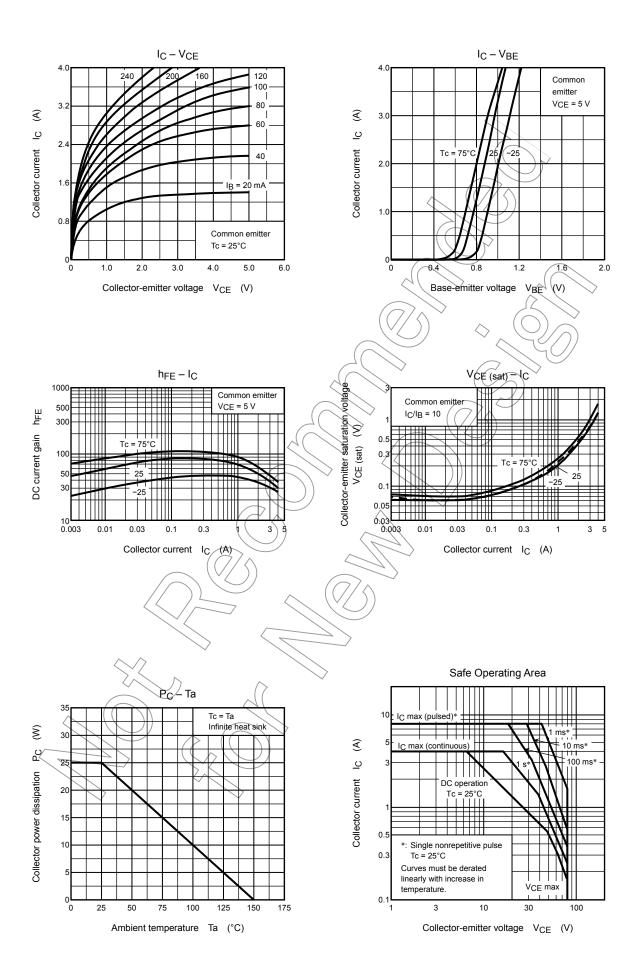
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 80 V, I _E = 0	_	_	30	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	100	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	80	_	-	٧
Emitter-base breakdown voltage	V _(BR) EBO	I _E = 10 mA, I _C = 0	5		-	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 5 V, I _C = 0.5 A	70) _	240	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 3 A	15	50	_	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 3 A, I _B = 0.3 A	_	0.45	1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 3 A	_	1.0	1.5	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 0.5 A	_	8.0		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		<\90	\rightarrow	pF

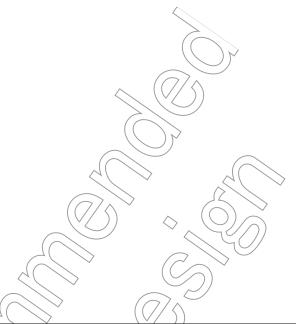
Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240





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RESTRICTIONS ON PRODUCT USE

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